2N3903 is a Preferred Device

General Purpose Transistors

NPN Silicon

Features

• Pb-Free Packages are Available*



Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	40	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter – Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	I _C	200	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	625 5.0	mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	1.5 12	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS (Note 1)

Characteristic		Symbol	Max	Unit
Thermal Resistance, Junction-to-	Ambient	$R_{\theta JA}$	200	°C/W
Thermal Resistance, Junction-to-	$R_{\theta,IC}$	83.3	°C/W	

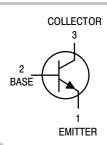
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

Indicates Data in addition to JEDEC Requirements.



ON Semiconductor®

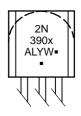
http://onsemi.com







MARKING DIAGRAMS



x = 3 or 4

A = Assembly Location

L = Wafer Lot Y = Year

W = Work Week
■ Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

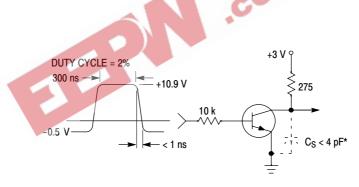
	Characteristic		Symbol	Min	Max	Unit
OFF CHARACTERIS	OFF CHARACTERISTICS					
Collector - Emitter Br	eakdown Voltage (Note 2) ($I_C = 1.0 \text{ mAdc}, I_B =$	0)	V _{(BR)CEO}	40	-	Vdc
Collector - Base Brea	akdown Voltage (I _C = 10 μAdc, I _E = 0)		V _{(BR)CBO}	60	-	Vdc
Emitter – Base Break	down Voltage ($I_E = 10 \mu Adc, I_C = 0$)		V _{(BR)EBO}	6.0	-	Vdc
Base Cutoff Current	(V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		I _{BL}	-	50	nAdc
Collector Cutoff Curr	ent (V _{CE} = 30 Vdc, V _{EB} = 3.0 Vdc)		I _{CEX}	-	50	nAdc
ON CHARACTERIST	rics					
DC Current Gain (No (I _C = 0.1 mAdc, V _{CE}		2N3903	h _{FE}	20	_	-
$(I_C = 1.0 \text{ mAdc}, V_{CE})$	= 1.0 Vdc)	2N3904 2N3903		40 35	-	
$(I_C = 10 \text{ mAdc}, V_{CE} =$	= 1.0 Vdc)	2N3904 2N3903 2N3904		70 50 100	150 300	
$(I_C = 50 \text{ mAdc}, V_{CE} =$	= 1.0 Vdc)	2N3903		30	-	
$(I_C = 100 \text{ mAdc}, V_{CE})$	= 1.0 Vdc)	2N3904 2N3903 2N3904	.0	60 15 30	_ _ _	
Collector – Emitter Sa ($I_C = 10 \text{ mAdc}, I_B = 1$ ($I_C = 50 \text{ mAdc}, I_B = 5$	aturation Voltage (Note 2) .0 mAdc) 5.0 mAdc	. %	V _{CE(sat)}	- -	0.2 0.3	Vdc
Base – Emitter Satura ($I_C = 10 \text{ mAdc}, I_B = 1$ ($I_C = 50 \text{ mAdc}, I_B = 5$		TO Y	V _{BE(sat)}	0.65 -	0.85 0.95	Vdc
SMALL-SIGNAL CH	IARACTERISTICS	10				
Current-Gain - Ban (I _C = 10 mAdc, V _{CE} =	dwidth Product = 20 Vdc, f = 100 MHz)	2N3903 2N3904	f _⊤	250 300		MHz
Output Capacitance	$(V_{CB} = 5.0 \text{ Vdc}, l_E = 0, f = 1.0 \text{ MHz})$		C _{obo}	_	4.0	pF
Input Capacitance (V	(EB = 0.5 Vdc, I _C = 0, f = 1.0 MHz)		C _{ibo}	-	8.0	pF
Input Impedance (I _C = 1.0 mAdc, V _{CE}	= 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{ie}	1.0 1.0	8.0 10	kΩ
Voltage Feedback Ra (I _C = 1.0 mAdc, V _{CE}	atio = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{re}	0.1 0.5	5.0 8.0	X 10 ⁻⁴
Small–Signal Curren ($I_C = 1.0 \text{ mAdc}, V_{CE}$	t Gain = 10 Vdc, f = 1.0 kHz)	2N3903 2N3904	h _{fe}	50 100	200 400	_
Output Admittance (I	C = 1.0 mAdc, V _{CE} = 10 Vdc, f = 1.0 kHz)		h _{oe}	1.0	40	μmhos
Noise Figure (I _C = 100 μ Adc, V _{CE}	= 5.0 Vdc, R_S = 1.0 k Ω, f = 1.0 kHz)	2N3903 2N3904	NF	- -	6.0 5.0	dB
SWITCHING CHARA	ACTERISTICS					
Delay Time	(V _{CC} = 3.0 Vdc, V _{BE} = 0.5 Vdc,		t _d	_	35	ns
Rise Time	I _C = 10 mAdc, I _{B1} = 1.0 mAdc)		t _r	-	35	ns
Storage Time	$(V_{CC} = 3.0 \text{ Vdc}, I_{C} = 10 \text{ mAdc}, I_{B1} = I_{B2} = 1.0 \text{ mAdc})$	2N3903 2N3904	t _s	- -	175 200	ns
Fall Time			t _f	_	50	ns

^{2.} Pulse Test: Pulse Width \leq 300 μ s; Duty Cycle \leq 2%.

ORDERING INFORMATION

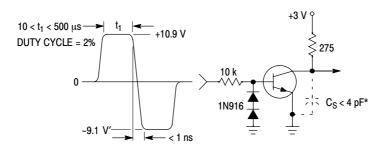
Device	Package	Shipping [†]
2N3903RLRM	TO-92	2000 / Ammo Pack
2N3904	TO-92	5000 Units / Bulk
2N3904G	TO-92 (Pb-Free)	5000 Units / Bulk
2N3904RLRA	TO-92	2000 / Tape & Reel
2N3904RLRAG	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904RLRM	TO-92	2000 / Ammo Pack
2N3904RLRMG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RLRP	TO-92	2000 / Ammo Pack
2N3904RLRPG	TO-92 (Pb-Free)	2000 / Ammo Pack
2N3904RL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
2N3904ZL1	TO-92 2000 / Ammo Pack	
2N3904ZL1G	TO-92 (Pb-Free)	2000 / Ammo Pack

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



^{*} Total shunt capacitance of test jig and connectors

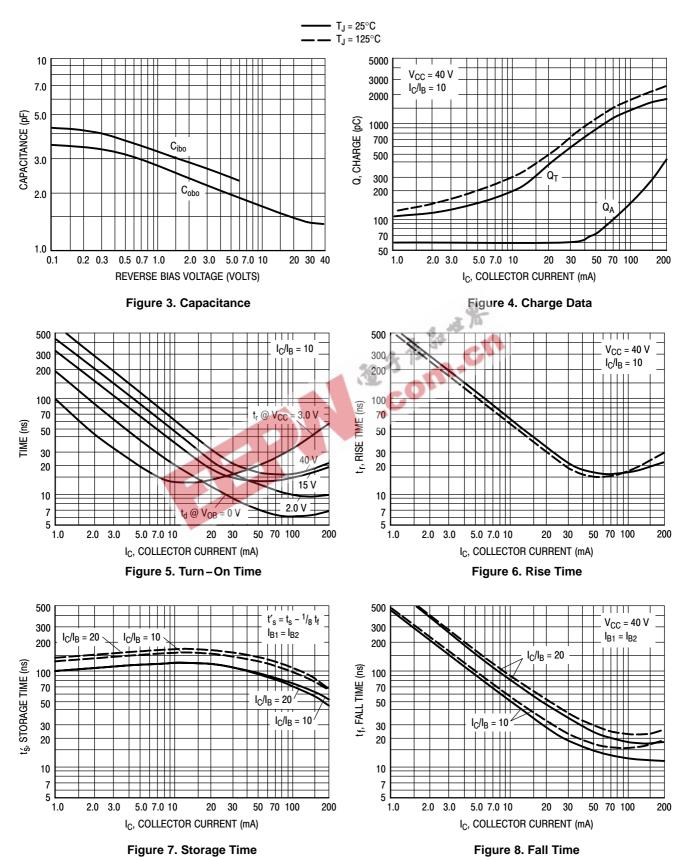
Figure 1. Delay and Rise Time Equivalent Test Circuit



^{*} Total shunt capacitance of test jig and connectors

Figure 2. Storage and Fall Time Equivalent Test Circuit

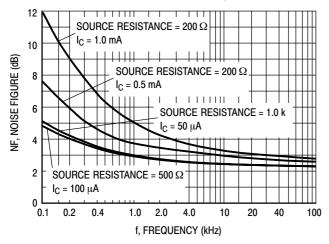
TYPICAL TRANSIENT CHARACTERISTICS



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TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS NOISE FIGURE VARIATIONS

 $(V_{CE} = 5.0 \text{ Vdc}, T_A = 25^{\circ}\text{C}, Bandwidth = 1.0 \text{ Hz})$



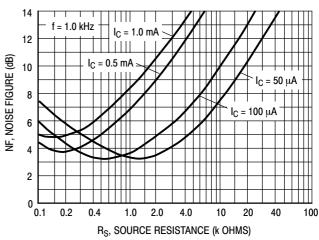
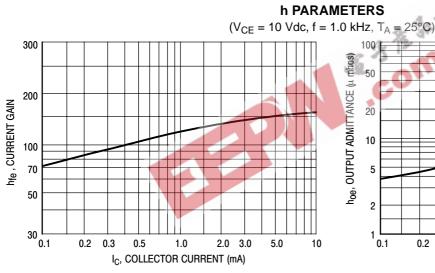


Figure 9.

Figure 10.



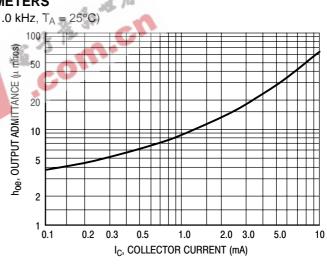
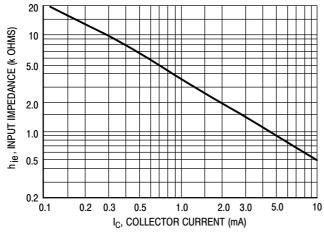


Figure 11. Current Gain

Figure 12. Output Admittance





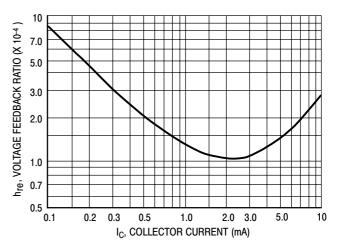


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

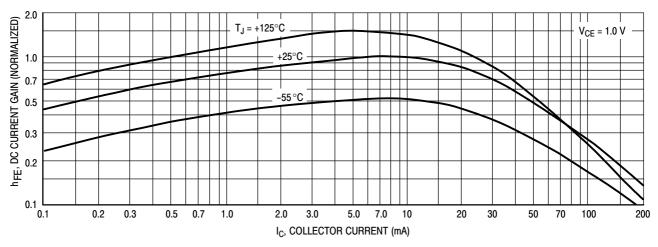


Figure 15. DC Current Gain

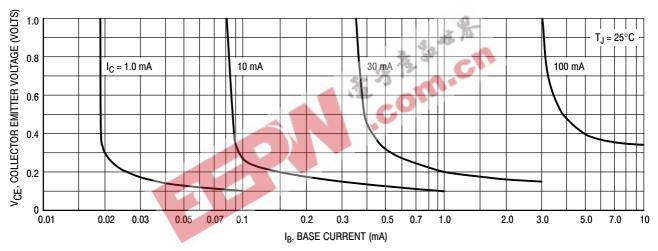


Figure 16. Collector Saturation Region

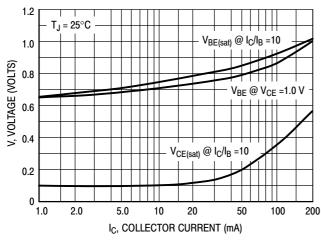


Figure 17. "ON" Voltages

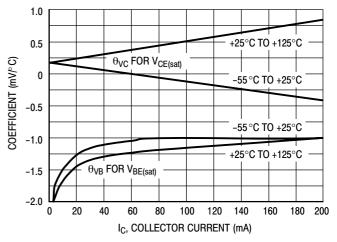
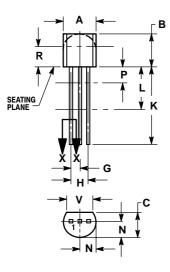


Figure 18. Temperature Coefficients

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 **ISSUE AM**



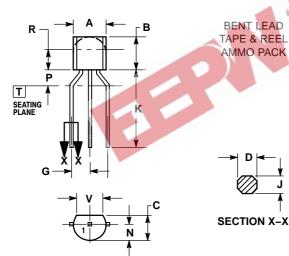
STRAIGHT LEAD **BULK PACK**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: INCH.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

		INCHES		MILLIMETERS	
	DIM	MIN	MAX	MIN	MAX
	Α	0.175	0.205	4.45	5.20
	В	0.170	0.210	4.32	5.33
	С	0.125	0.165	3.18	4.19
	D	0.016	0.021	0.407	0.533
	G	0.045	0.055	1.15	1.39
	Н	0.095	0.105	2.42	2.66
	J	0.015	0.020	0.39	0.50
	K	0.500		12.70	
	L	0.250		6.35	
	N	0.080	0.105	2.04	2.66
,	P		0.100		2.54
(R	0.115	and the second	2.93	
	V	0.135		3.43	
多为节		·C	n		
	NOTES	-			
	1. DI	MENSION	IING AND	TOI FRAI	NCING P



- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- CONTOUR OF PACKAGE BEYOND
 DIMENSION R IS UNCONTROLLED.
 LEAD DIMENSION IS UNCONTROLLED IN P
- AND BEYOND DIMENSION K MINIMUM

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
С	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93	-	
٧	3.43		

STYLE 1:

PIN 1. EMITTER

COLLECTOR

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